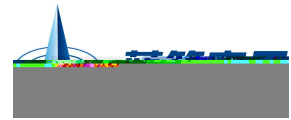


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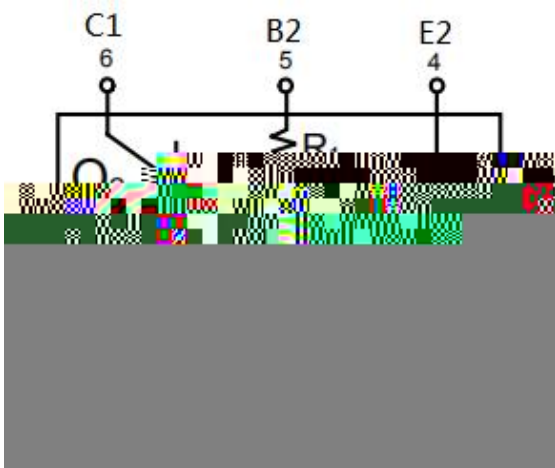


DATA SHEET

SOT-363 NPN+PNP
Double silicon NPN and PNP transistor in a SOT-363 Plastic Package

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process, Halogen-free Product.

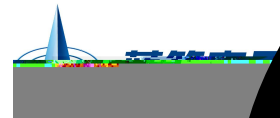
Switching applications, interface circuit and driver circuit applications.



放大及印章代码 / h_{FE} Classifications & Marking

Marking

H314

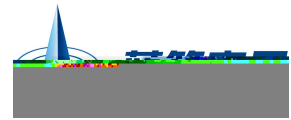


Parameter	Symbol	Rating	Unit
Output Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	40	V
		-6	V
Output Current	I_C $I_{(on)}$	100	mA
	I_O $I_{O(on)}$	70	mA
Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Max	Unit	
Input Voltage(OFF)	$V_{I(off)}$	$v_{CC}=5.0V$ $I_O=100\mu A$		0.3	V	
Input Voltage(ON)	$V_{I(on)}$	$V_O=0.3V$ $I_O=1mA$	1.4		V	
Output Voltage	$V_{O(on)}$	$I_O=5mA$ $I_I=0.25mA$		0.1	0.3	V

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电参数曲线图 / Electrical Characteristic Curve(NPN)



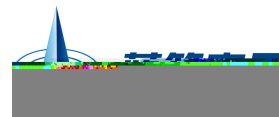
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印章说明 / Marking Instructions

H314**
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● " 1"

H314

***:

Note:

● "1" Pin

H314 Product Type Code

***: Lot No. Code, code change with Lot No.

